### ETHERNET TRANSCEIVER ELECTRICAL CHARACTERISTICS

#### 1.0 Station

- 1.1 Input: XDATA
  - 1.11 Resistance: 132 ohms nominal
  - Logic: Negative ("0" volt) true
  - 1.13 Interface: 5 volt TTL compatible
- 1.2 Outputs:- TROTHER & TRDATA
  - Type of drive: Open collector
  - Low state current sinking: 48 ma max. 1.22
  - Logic: Positive (≥ 2 volts) true 1.23
  - 1.24 Interface: 5 volt TTL compatible

### 2.0 Ether

- 2.1 Input:- ETHER

  - 2.11 Resistance: ≥ 100k ohms 2.12 Capacitance: ≤ 10pf 2.13 Bias current: ≤ -15ua
  - 2.14 Max. input voltage without damage: +10 volts, -.4 volts
- 2.2 Output: ETHER
  - 2.21 Drive voltage: +3 volts (Nominal) into 37.5 ohms
  - 2.22 Rise & Fall times: 12ns typical
  - 2.23 Waveform: Pulse
- 2.3 Power shut down at output incase of catastrophic failure at output stage!
- 3.0 Transceiver
  - 3.31 Frequency range: 1.3 MHz to 3.3 MHz
  - Duty cycle range: 30% to 70% or 140 ns whichever is closer to 50% 3.32
  - 3.33 Waveform: Pulse
  - 3.34 Ether ground potential noise immunity: 50 volts DC reducing
- 3.35 Power requirement: +15 volts + 2% @ 80 ma (typical)
  +5 volts + 5% @ 110 ma (typical)

  3.36 Operating temperature: 10°C to 40°C

  3.37 Storage temperature: 0°C + 5°C

  3.37 Storage temperature: 0°C + 5°C

  3.37 Storage temperature: 0°C + 5°C

  3.38 Storage temperature: 0°C + 5°C

  3.39 Storage temperature: 0°C + 5°C

  3.30 Storage temperature: 0°C + 5°C

  3.30 Storage temperature: 0°C + 5°C

  3.31 Storage temperature: 0°C + 5°C

  3.32 Storage temperature: 0°C + 5°C

  3.33 Storage temperature: 0°C + 5°C

  3.34 Storage temperature: 0°C + 5°C

  3.37 Storage temperature: 0°C + 5°C

  3.38 Storage temperature: 0°C + 5°C

  3.39 Storage temperature: 0°C + 5°C

  3.30 Storage temperature: 0°C

  3.30 Storage temperature: 0°C

  3.30 Storage temperature: 0°C

  3.30 St
- 3.37 Storage temperature: 0°C to 50°C 3.38 Size: 24" H x 4" W x 24" D

## ETHERNET STATION PARTS LIST

Ckt No.	Mfr	Part No.	Description	
Resistors indicated.		composition/film	$\frac{\pm 5\%}{1}$ , $\frac{1}{4}$ watt unless of	herwise
R1 B2 B3 B4 B5			680 ohm 4.7k 1.8k 2.2k 270	
R6 R7 R8 R9			150 680 3.9k 470 470	
R11 R12 R13 R14 R15			27k 2.7k 1k 330 220	
Capacitors				
C1 C2 C3 C4 C5	Sp 1	DM-19-102J DM-15-270J 96D106X9020JA1 96D106X9020JA1 96D106X9020JA1	Mica 1000pf 5% 500v Mica 27pf 5% 500v Tantalum 10uf 10% 20v Tantalum 10uf 10% 20v Tantalum 10uf 10% 20v	
<b>0</b> 6 <b>C7</b>	Sp 1	96D106X9020JA1 DM-15-221J	Tantalum 10uf 10% 20v Mica 220pf 5% 500v	
Inductor				
Ll			150uH	
Transforme.	rs			
T1 T2 T3			Power transformer Coupling transformer Coupling transformer	
Semiconduc	tor device:			
D1 D2	TI TI	1N914 1N914	Diode Diode	
21 22	TI TI	TIP3055 TIP3055	NPN power transistor NPN power transistor	
IC1 IC2 IC3	TI TI TI	SN75140P SN7438N SN7404N	Dual line receivers Quad 2-Input + NAND Buff Hex Inverters	ers

# ETHERNET ETHER PARTS LIST

Part No.

Ckt No: Mfr

Description

Resistors are indicated.	fixed,	compositio	n/film,	<u>+</u> 5%, 1/	4 watt	unless	other
R101 R102 R103 R104 R105	2 3			1k 686 27 27 156	0		
R106 R107 R108 R109 R110				686 4.7 -101 1k 4.7	7 <b>k</b> K		
R111 R112 R113 R114 R115				330 1k 1k 1k 3.			
R116 R117 R118 R119 R120				4.1 1.5 181 100 220	k )		
R121 Capacitors				lk			
C101 E1 C102 E1 C103 Sp C104 Sp C105 Sp	DM-1 196D106 196D106	15-270J 19-102J 5X9020JA1 5X9020JA1 5X9020JA1	Tanta Tanta	27pf 5 1000pf 5 lum 10ui lum 10ui lum 10ui	10% 2 10% 2	7 20 <b>v</b> 20 <b>v</b>	
C106 Sp C107 Sp		5X9020JA1 -360		lum loui		20 <b>v</b>	
Semiconductor	Devices						
CR101 F CR102 TI CR103 TI CR104 TI CR105 TI		LN4610 LN914 LN4001 LN914 LN914		Diode Diode Diode Diode			

## ETHERNET ETHER PARTS LIST

Ckt No.	Mfr	Part No.	Description
CR1.06	TI	ln914	Diode
CR107	TI	1N914	Dioae
CR108	TI	1N914	Dioae
CR109	TI	1N914	Diode
CR110	<b>ग</b> ण	1N)14	Diode
CRILL	ŤI	1N914	Diode
CR112	ŤĪ	1N914	Diode
CR113	TI	1N914	Diode
2101	F	2N5771	PNP transistor
จี102	F	2N4275	NPN transistor
1103	P	ZN4275	NPW transistor
2104	F	2N4275	NPN transistor
2105	GE	D43C2	PNP transistor
IC101	TI	SN75140P	Dual line receivers
TC102	Sig	N8T14B	Triple line receivers
LED101	Mon	<b>W</b> 5024	Red light emitting diode

### \*Note:

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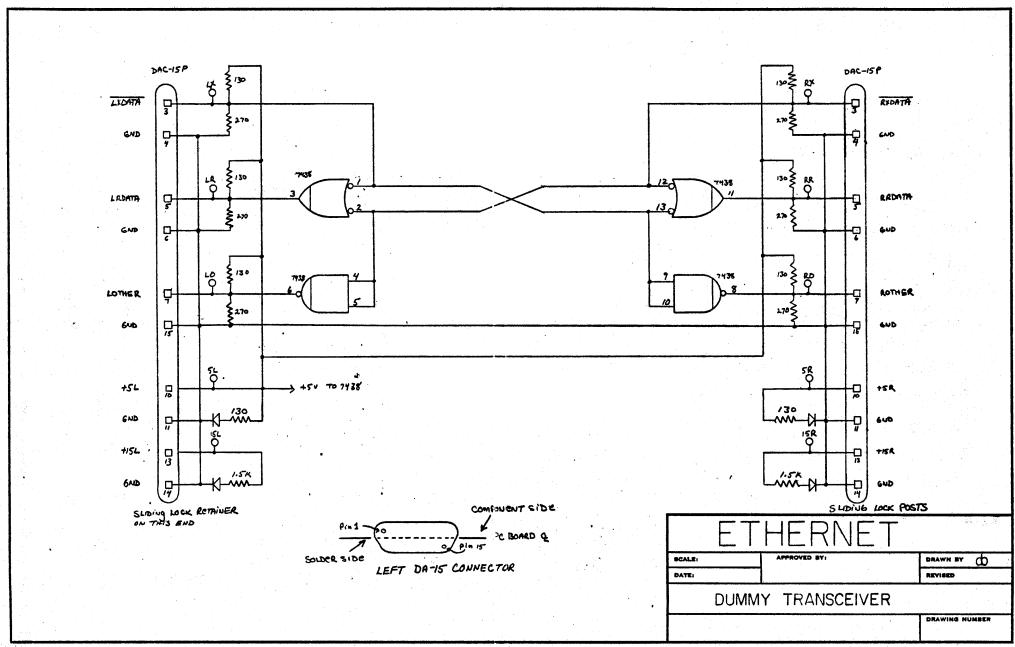
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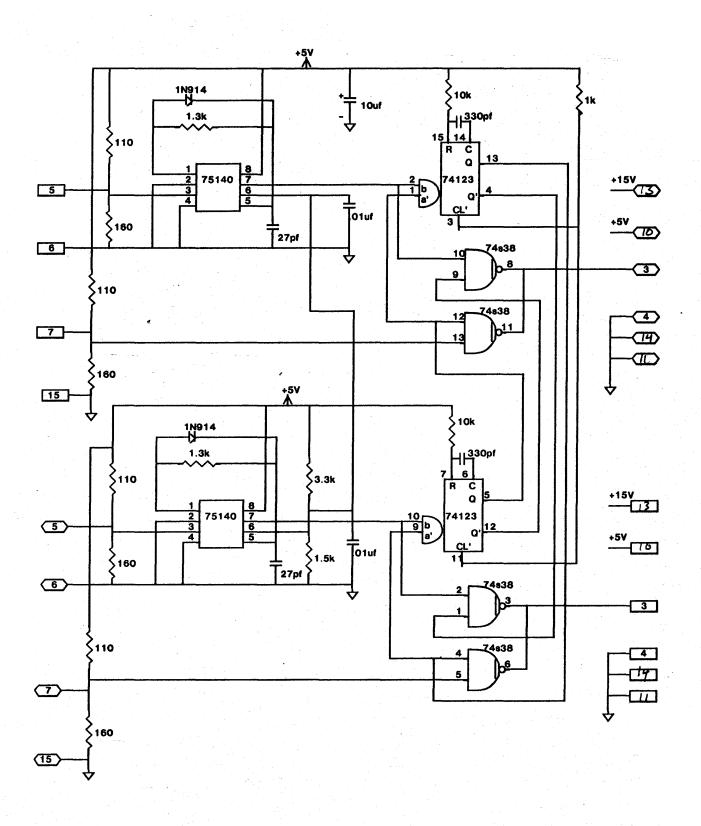
Sprague Electric Co. TĪ

Texas Instruments, Inc. Semiconductor div. Fairchild Camera & Instrument Corp. Semiconductor div. F

General Electric Co. Semiconductor div. GE

Sig Signetics Corp.
Mon Monsanto Co. LED div.

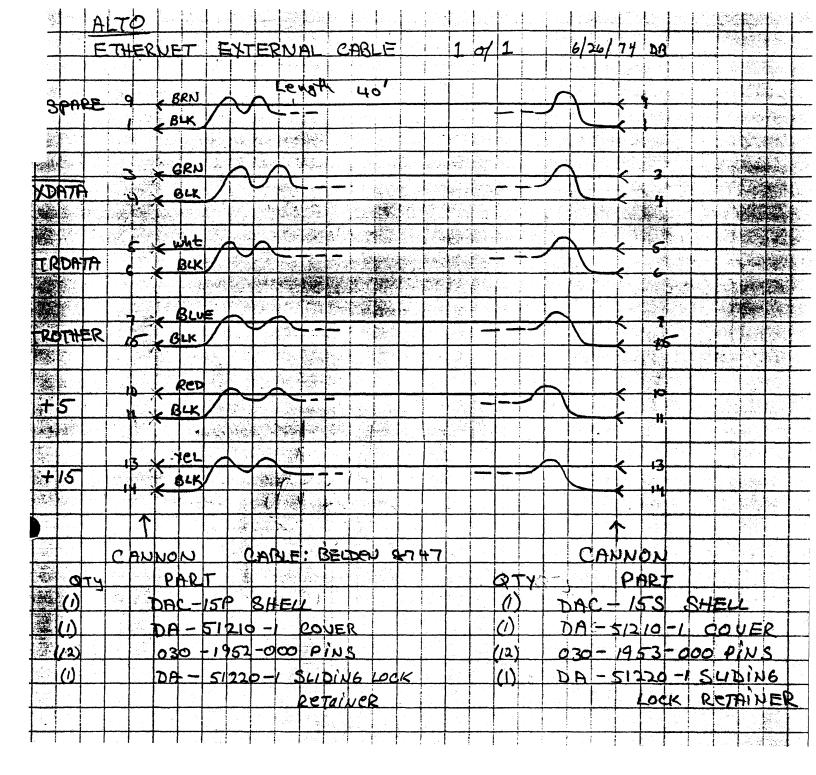


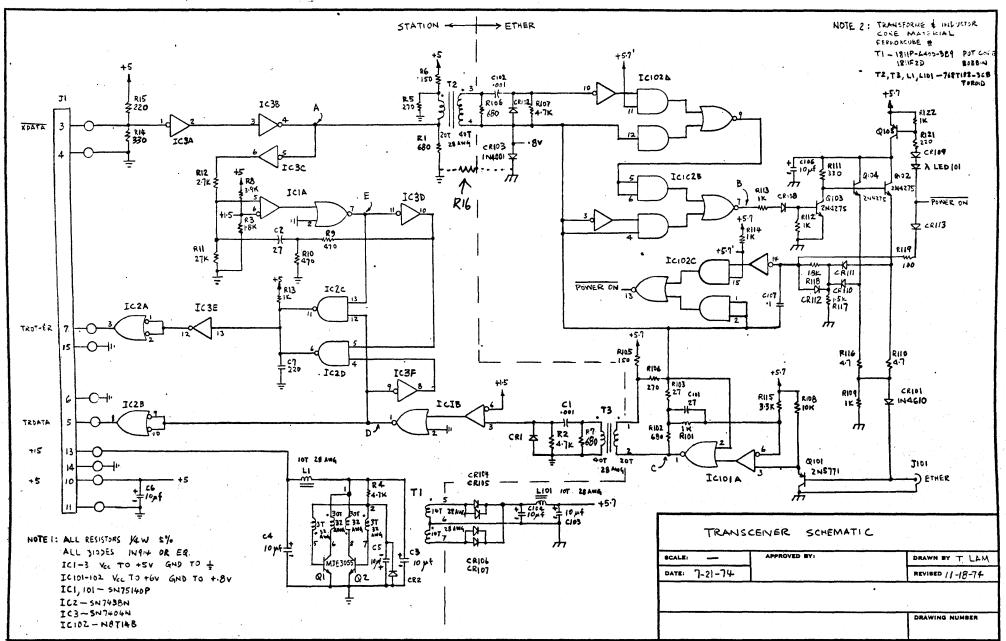


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PARC		ETHERNET REPEATER	REPEATER	D BGGS	В	4-8-78	. 1	

	Wire No.	Term	From	То	Term	wire Type	Notes A Company	Signal	Chg. Let.
Γ		3	PI-9	P.Z-9	5	ı	BRN ) TWISTED	SPARE	
	2					1	BLK 3 PAIR	SPARE	
	3		3	3			GRN	XDATA	
	4		4	4			BLK	XDATA	
	Б		5	5			WHT	TROATA	
	6		6	6			BLK	TROSTA	
	7	`	7	7			BLU	TROTHER	
Γ	8		15	15			BLK	TROTHER	
	9		10	10			RED	+57	
Ī	10		1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1				BLK	+50	
	11		13	13			YEL? TWISTED	+150	
Ī	12	3	P1-14	PZ-14	5	1	BLKS PAIR	+157	
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도<sup>속</sup>이 하되는 사람들은 사람들은 경험을 보냈다.





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